Spin-Valley Polarized Quantum Anomalous Hall Effect and a Valley-Controlled Half Metal in Bilayer Graphene

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We investigate topological phases of bilayer graphene subject to antiferromagnetic exchange field, interlayer bias, and irradiated by light. We discover that at finite bias and light intensity the system transitions into a previously unknown spin-valley polarized quantum anomalous Hall (SVP-QAH) insulator state, for which the subsystem of one spin is a valley Hall topological insulator (TI) and that of the other spin is a QAH insulator. We assess the TI phases occurring in the system by analytically calculating the spin-valley dependent Chern number, and characterize them by considering edge states in a nanoribbon. We demonstrate that the SVP-QAH edge states lead to a unique spin rectification effect in a domain wall. Along the phase boundary, we observe a bulk half-metal state with Berry’s phase of $2\pi$.

\textit{Introduction.} Bernal-stacked bilayer graphene (BLG) consists of two honeycomb lattices coupled by van der Waals interaction [1]. Due to its novel electronic properties, such as low-energy states with Berry’s phase of [2] $2\pi$ and an electrically-tunable band gap [3, 4], BLG has recently attracted much attention both theoretically and experimentally, see e.g. Refs. 5–10. In particular, BLG became popular for studies of phenomena related to the valley degree of freedom [9, 11–14], resulting in discovery of non-trivial topological states of matter. Recently, a striking finding was the discovery of the quantum valley Hall (QVH) effect in BLG, for which the edge states in the gap driven by an interlayer bias are valley-polarized and provide the conductance quantization with the step of [15–18] $4e^2/h$. Theoretical studies have predicted that the usual QVH insulator in BLG undergoes a transition to a valley-polarized quantum spin Hall insulator under effect of Rashba spin-orbit interaction [19, 20].

Another attractive topological state of matter is the quantum anomalous Hall (QAH) state, generally characterized by chiral edge states in the gap and nonzero charge Chern numbers [21–23]. The QAH state in BLG has been suggested to be induced by Rashba interaction and internal magnetization [24] or by strong circularly polarized light [25–27], differently from the mechanism of Landau-level quantization in quantum Hall effect. Most recently, the valley-polarized QAH state possessing the properties of both the QVH and QAH states has been proposed in other 2D systems [28, 29] similar to BLG. Interestingly, this QAH state can possess edge states which are not completely chiral [28].

In this Letter, we present the light and voltage controlled phase diagram of BLG in contact with layered antiferromagnetic (AFM) exchange field and discover a variety of topological insulator (TI) states in this system. We argue that this AFM BLG itself is a quantum anomalous valley Hall (QVAH) insulator [30], that it undergoes a transition to a usual QVH insulator as interlayer bias increases, and that it is switched to a normal QAH (N-QAH) insulator, a system with chiral edge states, as light intensity increases. Remarkably, we discover that if both voltage and light are applied, the system can be in a spin-valley polarized QAH (SVP-QAH) insulator state, for which the subsystem of one spin is in a QVH state and that of the other spin is in a QAH state. To our knowledge, this state has not been previously described in the literature and it is distinct from the single-valley spin-polarized QAH states [26, 29] and the QAH states with no spin or valley polarizations [13–17, 21–23, 28].

The TI states in the system are discriminated by the spin-valley dependent Chern number [9], which we calculate analytically. We further characterize these TIs by edge states in a zigzag ribbon and show transport differences in domain walls. In the phase boundary, we discover that the 2D bulk system can host a half-metal state with Berry’s phase of $2\pi$, and the number of gap-closing valleys is tunable.

\textit{Hamiltonian.} The BLG system we consider is described by the eight-band tight-binding model

$$\hat{H} = -J \sum_{\langle i,j \rangle, \alpha} c_{i \alpha}^{\dagger} c_{j \alpha} - \gamma \sum_{\langle i, j \rangle, \alpha} c_{i \alpha}^{\dagger} c_{j \alpha} + M \sum_{\alpha} \mu_{\alpha} c_{i \alpha}^{\dagger} \sigma_{z} c_{i \alpha}$$

$$- U \sum_{\langle i, j \rangle, \alpha} \mu_{\alpha} c_{i \alpha}^{\dagger} c_{i \alpha} + \frac{i}{3\sqrt{3}} \sum_{\langle i, j \rangle, \alpha} \nu_{ij} c_{i \alpha}^{\dagger} c_{j \alpha},$$

where $c_{i \alpha}^{\dagger}$ creates an electron with spin polarization $\alpha$ at site $i$, and $\langle i, j \rangle/\langle\langle i, j \rangle\rangle$ run over all the nearest and next nearest neighbor hopping sites. The subscript $||$ (\perp) denotes “in plane” (“out of plane”), $\mu_{\alpha} = \pm 1$ indicates that site $i$ lies in the bottom (top) layer, $\sigma_{z}$ is the z-component of Pauli matrix in the spin subspace, and $\nu_{ij} = +1 (-1)$ holds if the next nearest hopping is anticlockwise (clockwise). In Eq. (1), the first and second terms are the intralayer and interlayer nearest neighbor hoppings with [8] $J = 3.0$ eV and $\gamma = 0.39$ eV. The third term, $H_{M}$, is the layered AFM exchange field, which can be applied by depositing BLG between 2D magnetic insulators CrI$_3$ [30] ($M \sim 7$ meV can be achieved). The fourth term, $H_{\mu}$, is the interlayer bias with $U$ being up to 125 meV in experiment [4, 7]. The fifth term, $H_{\nu}$, is the Haldane mass term [31], which can be applied [26] by irradiating BLG with circularly polarized light (see Supplemental Material [32] and Refs. [33, 34]). Estimated from the band width in BLG, the
light frequency would typically lie in the range \(10^{13} - 10^{14}\) Hz, leading to the estimate of \(\lambda \approx 10\) meV.

**Topological theory.** The QAH effect is characterized by the charge Chern number [21–24, 28]

\[
C = \frac{1}{2\pi} \sum_n \int_{BZ} d^2k \Omega_n(k),
\]

where \(\Omega_n\) is the momentum-space Berry curvature [9] in the out-of-plane direction for the n-th subband.

\[
\Omega_n(k) = -\sum_{n' \neq n} 2\text{Im}\langle \psi_{nk}| \nabla_{\kappa} |\psi_{n'k}\rangle \langle \psi_{n'k}| \nabla_{\kappa} |\psi_{nk}\rangle / (\varepsilon_{n'} - \varepsilon_n)^2.
\]

The summation is over all occupied valence bands in the first Brillouin zone below the bulk band gap, \(\psi\) is the Bloch state, and \(v_{x(y)}\) is the velocity operator along the x(y) direction.

One can label a state a TI if it has at least one nonzero topological invariant [24–27, 29–31, 33, 34]. Because electrons in BLG here have a mixture of charge, spin and valley degrees of freedom, the index \(C\) can not identify the spin or valley polarized TI phases. To solve this problem, we employ a decomposed, spin and valley dependent Chern number [9, 34] \(C'_n\), which is well defined in half of the first Brillouin zone around \(K\) \((\eta = +1)\) or \(K'\) \((\eta = -1)\) points for spin-up \((s = +1)\) or spin-down \((s = -1)\) electrons. On basis of \(C'_n\), the spin and valley Chern numbers [9] can be defined as \(C_s = C_{K} - C_{K'} = \sum_{\alpha} (C_{K\alpha}^{s} - C_{K'\alpha}^{s})\), respectively. The charge Chern number satisfies \(C = \sum_{\eta,s} C'_n\).

**Phase diagram.** We present our result as the phase diagram in Fig. 1 by tuning \(U\) and \(\lambda\). The topological numbers \((C, C'_n)\) are used to index the TI phases, including QAVH, QVH, N-QAH and SVP-QAH. We show how to derive the analytical expressions for the phase boundary and the Chern numbers from low-energy theory later. Because the sign changes of \(U\) and \(\lambda\) only influence the signs of Chern numbers (no novel phases appear), one only needs to characterize the phases for \((U \geq 0, \lambda \geq 0)\). To describe the edge states, some typical cases are chosen to calculate the bands in a zigzag ribbon (Supplemental Material [32]). The edge states in real space for each TI are illustrated in Figs. 2(a)-2(d), where the moving directions (hollow arrows) for electrons agree with Eqs. (9–12). At the phase boundary, the bulk gap closes [Eq. (6)].

We first discuss the QAVH state, for which \((C, C'_n) = (0, \eta s)\) [30]. The nonzero value of \(C'_n\) in this phase arises from the inversion symmetry breaking dominated by \(M\). Although the QAVH phase has metallic in-gap edge states near \(K\) and \(K'\), the index \(C\) is zero. The anomalous property of the state is that the subsession of each spin is a QVH insulator \([C'_s = C'^{K}_s - C'^{K'}_s = 2\text{ in Fig. 2(a)},\) while the whole system is not valley polarized \((C_v = 0)\). The result \(C'^{K}_s + C'^{K'}_s = 0\) indicates the edge states in each valley behaves as a quantum spin Hall state [19, 22] in spite of \(C_v = 0\). If we include non-zero voltage \(U\), the system eventually undergoes a transition to a normal QVH insulator \([C_v = -4\text{ in Fig. 2(b)}]\) due to the competition of \(U\) and \(M\). The QAVH insulator transitions to an N-QAH insulator \([C = 4\text{ in Fig. 2(c)}]\) as \(\lambda\) increases due to the time-reversal symmetry breaking. Each transition is associated with with a process of the closing and reopening of the gap.

Our most significant result is the SVP-QAH phase, which appears in regions where \(U\) and \(\lambda\) are non-zero and occupies a major part of the phase diagram. For a SVP-QAH state, four spin-down edge states in the gap appear near \(K\) and \(K'\), but four spin-up edge states appear away from \(K\) and \(K'\) [Figs. 2(d) and 2(g)]. Correspondingly, the Berry curvature in the \((k_x, k_y)\) plane [Fig. 2(e)] and specifically along \(K-K'\) direction [Fig. 2(f)] is shown. We find that the spin-down subsystem is a QVH insulator \([C'_s = -C'_v = -1, C'_s = C'_v = 0],\) whereas the spin-up subsystem is a normal QAH insulator \([C'_s = C'_v = 1, C'_s = 0, C'_s = C'^{K}_s + C'^{K'}_s = 2],\) and then \(C = C'_s + C'_v = 2\) is achieved. To our knowledge, this SVP-QAH insulator is a new type of a QAH state, which differs obviously from the single-valley spin-polarized QAH [26, 29], spin-unpolarized QAH [9, 12–14, 28], and valley-unpolarized QAH [9, 22, 34] states discovered previously.

At the phase boundaries, see bold lines in Fig. 1, there exists a 2D bulk state that is half-metallic [35] (gap closing at \(K\) or \(K'\)), as shown by the completely spin-polarized band structures (bottom) near the Fermi level for the marked points \(a\) and \(b\). In contrast, point \(a\) corresponds to a dual-valley half-metal (valley degeneracy), while point \(b\) refers to a single-valley...
half-metal (the other valley is insulating). For the marked point $c$, spin-down (spin-up) subbands near the Fermi level are locked to the $K$ ($K'$) valley, resulting in a spin-valley locked semimetal. Thus gap closing of the valleys in which one or two is tunable. Notably, the bulk half-metal state here has the Berry’s phase of $2\pi$ [Eq. (8)].

Low-energy formalism. To further explore the physics underlying the phase diagram, we analyze the low-energy effective Hamiltonian derived from the lattice model (1) after Fourier transformation, and reveal the physics of electrons near $K$ and $K'$. For simplicity, we set $\hbar = 1$ and $v_F = 1$ below. Because two opposite spins are decoupled in Eq. (1), the effective Hamiltonian can be written as a $4 \times 4$ matrix

$$
H = \begin{pmatrix}
\Delta_{yy} - U, & \eta k_x - i k_y, & 0, & 0 \\
\eta k_x + i k_y, & -\Delta_{yy} - U, & -\gamma, & 0 \\
0, & -\gamma, & \Delta_{yy} + U, & \eta k_x - i k_y \\
0, & 0, & \eta k_x + i k_y, & -\Delta_{yy} + U
\end{pmatrix},
$$

(4)

where $\Delta_{yy} = \eta \lambda \pm sM$. Note that $s$ and $M$ only occur as a product $sM$, and thus the reversal of the sign of $M$ is equivalent to the reversal of spin orientation. We will assume $M > 0$. By matrix diagonalization, we derive the band structure as

$$
\varepsilon = \pm \sqrt{k^2 + (sM - U)^2 + \lambda^2 + \frac{1}{2} \gamma^2 \pm \sqrt{\Gamma_k}},
$$

(5)

$$
\Gamma_k = k^2 [16(sM - U)^2 + 4\gamma^2] + [\gamma^2 - 4\eta\lambda(sM - U)]^2.
$$

(6)

Note that the electron-hole symmetry is present in Eq. (5), from which one can prove that the gap is closed only under $\varepsilon = 0$, which requires $k = 0$ [at $K(K')$] and simultaneously

$$
U = sM + \eta \lambda.
$$

(7)

According to the topological theory [9], this gap-closing condition in Eq. (6) precisely describes the phase boundary as given in Fig. 1. Specifically at $k = 0$, the energy gap reads

$$
\Delta_{\eta}^2 = 2 \sqrt{(sM - U)^2 + \lambda^2 + \frac{1}{2} \gamma^2 - 4|\eta\lambda(sM - U)|}.
$$

(8)

Judging from Eq. (6), the system is a dual-valley half-metal for $(\lambda, U) = (0, \pm M)$ and a spin-valley locked semimetal for $(\lambda, U) = (\pm M, 0)$. Except for these points, the system is a single-valley half-metal in the phase boundary. For the half-metal state, Hamiltonian (4) for specific spin recovers the single-valley half-metal Bloch state $\psi_{k,\phi} (\phi$ being the azimuthal angle of the momentum) here has the Berry phase [36]

$$
\varphi_B = i \int_0^{2\pi} d\phi \frac{\partial}{\partial \phi} |\psi_{k,\phi}\rangle = 2\eta \pi,
$$

(9)

which can induce a spin-polarized integer quantum Hall effect with a missing zero-level plateau [2].

Chern numbers and domain-wall transport. We see from Eq. (6), Fig. 1 and our band calculations [32] that the QAVH, QVH, N-QAH and SVP-QAH insulator states hold under $|\lambda| < M - |U|, |\lambda| < |U| - M, |\lambda| > |U| + M, |U| - M > |\lambda| > |U| + M$, respectively. Usually, the topological invariants are associated with the signs of the parameters for a TI state [9, 34]. For the QAVH, QVH, and N-QAH insulators here, the index $C_{\eta}^i$ is respectively determined by

$$
C_{\eta}^i = \eta s_i - \eta \text{sgn}(U), \text{ sgn}(\lambda)
$$

(10)

and correspondingly $C = C_S, C_C, C_0$ are expressed as

$$
C = 0, 0, 4\text{sgn}(\lambda) \parallel C_S = 0, 0, 0 \parallel C_C = 0, -4\text{sgn}(U), 0,
$$

(11)

where sgn$(x)$ is the sign function. For the SVP-QAH insulator, we calculate $C_{\eta}^i$ to be

$$
C_{\eta}^i = (\delta_{s,1} + \delta_{s,-1}) [\text{ sgn}(\lambda)\delta_{s,\text{sgn}(U)} + \eta \delta_{s,\text{sgn}(-U)}],
$$

(12)

and the other Chern numbers satisfy

$$
C = 2\text{sgn}(\lambda), C_s = 2\text{sgn}(U), C_0 = -2\text{sgn}(U).
$$

Here, $\delta_{s,\nu}$ is the Kronecker delta function. We see from Eqs. (9) and (11), $C_{\eta}^i = 1$ always holds for each TI case.

To distinguish and detect the SVP-QAH state, we consider a domain wall between AB- and BA-stacked GBL [15] in Fig. 3(a), where the conducting channels and band structure are shown when $\lambda$ has the opposite values in AB and BA regions. By using Green’s function method [37], we show the domain-wall conductance $G = I/V$, where $I(V)$ is the current...
conducting channels are shown for the AB(A)/BA(−A) case, where the band structure (bottom) is calculated for a sharp domain wall. The band gap satisfies \( \Delta = \min \Delta_s^s(g, s = \pm 1) \). (b) Domain-wall conductance within the gap in the AB(A)/BA(−A) domain walls. The solid, dashed, dot-dashed lines represent, respectively, the SVP-QAH, QAVH (the same for QVH) and N-QAH cases.

Note that all the QVH channels marked by \( K \) and \( K' \) in Figs. 2(a)-2(d) and 3(a) disappear along the armchair direction [9, 10, 12] when valley is not a good quantum number. Nevertheless, a unipolar spin diode [38] (only spin-up electrons are unidirectionally conducting for \( V > 0 \)) works if the domain wall is of the armchair type in Fig. 3(a).

Discussion. —Realization of the SVP-QAH state in BLG depends on the presence of the magnetic field term, \( H_M \), which is not induced by the electron-electron interaction [26] but by proximity, such as a van der Waals system consisting of BLG and magnetic insulator CrI\(_3\) [30] (\( M \sim 7 \) meV can be achieved). Possibilities of proximity induced by other 2D layered magnets in BLG, such as CrBr\(_3\) or Cr\(_2\)Ge\(_2\)Te\(_6\) [39], requires more research. Magnetic insulator EuS is an alternative candidate to induce \( H_M \) on basis of the experimental evidence for ferromagnetism in graphene [40]. Beyond model (1), the Coulomb interaction might induce a gap about 1 meV [7, 26], which is usually disregarded when other interactions are stronger [4, 15–17] as we concern in Eq. (1).

In particular, other photoinduced terms beyond \( H_A \) such as optical absorption and high-energy Floquet sidebands [34, 41, 42] can be safely ignored [25–27, 34] as we focus on the nearly off-resonant light above 10 THz. Because the light absorbance per graphene layer is only about 2.3% [43], the band population is presumably intact. For the SVP-QAH domain-wall transport in Fig. 3(a), the electron mean free path \( L_0 \sim 420 \) nm is verified by experiment [15–18]. Ignoring the contact resistance, the dependence of ballistic conductance \( G \) on domain-wall length \( L \) is determined by [15, 37]

\[
G = \frac{\zeta e^2}{h}(1 + L/L_0),
\]

where \( \zeta \) corresponds to the integer for quantized plateau as given in Fig. 3(b).

The topological transitions modulated by photon and electric voltage explored here will motivate the experimental exploration of novel 2D QAH insulators with rich spin or valley physics based on BLG as well as the integrated systems between layered 2D materials, van der Waals magnets and correlated valley materials, for which the combination of spintronics, valleytronics and topology promises discoveries of novel condensed matter phases.

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\[11\] W. Jaskólski, M. Pelc, G. W. Bryant, L. Chico, and A. Ayuela, 2D Mater. 5, 025006 (2018).
\[16\] J. Li, K. Wang, K. J. McFaul et al., Nanotechnol. 11, 1060 (2016).
\[26\] C. Qu, C. Zhang, and F. Zhang, 2D Mater. 5, 011005 (2018).